Doyeol Ahn

List of Publications by Citations

179 papers	3,132 citations	27 h-index	50 g-index
189 ext. papers	3,400 ext. citations	2.4 avg, IF	5.24 L-index

#	Paper	IF	Citations
179	Calculation of linear and nonlinear intersubband optical absorptions in a quantum well model with an applied electric field. *IEEE Journal of Quantum Electronics*, **1987**, 23, 2196-2204	2	340
178	Intersubband optical absorption in a quantum well with an applied electric field. *Physical Review B*, **1987**, 35, 4149-4151	3.3	164
177	. *IEEE Journal of Quantum Electronics*, **1988**, 24, 2400-2406	2	122
176	Theory of non-Markovian optical gain in quantum-well lasers. *Progress in Quantum Electronics*, **1997**, 21, 249-287	9.1	120
175	Intraband relaxation time effects on non-Markovian gain with many-body effects and comparison with experiment. *Semiconductor Science and Technology*, **2000**, 15, 203-208	1.8	105
174	Electronic and Optical Properties of ${rm a}$- and ${rm m}$-Plane Wurtzite InGaN□GaN Quantum Wells. *IEEE Journal of Quantum Electronics*, **2007**, 43, 1175-1182	2	103
173	. *IEEE Journal of Quantum Electronics*, **1990**, 26, 13-24	2	92
172	Spontaneous and piezoelectric polarization effects in wurtzite ZnO□MgZnO quantum well lasers. *Applied Physics Letters*, **2005**, 87, 253509	3.4	91
171	Relativistic entanglement and Bell□ inequality. *Physical Review A*, **2003**, 67,	2.6	90
170	Optical transitions in a parabolic quantum well with an applied electric field□nalytical solutions. *Journal of Applied Physics*, **1989**, 65, 2822-2826	2.5	81
169	Valence-band mixing effects on the gain and the refractive index change of quantum-well lasers. *Journal of Applied Physics*, **1988**, 64, 4056-4064	2.5	81
168	High-efficiency staggered 530 nm InGaN/InGaN/GaN quantum-well light-emitting diodes. *Applied Physics Letters*, **2009**, 94, 041109	3.4	77
167	Dip-shaped InGaN/GaN quantum-well light-emitting diodes with high efficiency. *Applied Physics Letters*, **2009**, 95, 063507	3.4	61
166	Dense coding in entangled states. *Physical Review A*, **2002**, 66,	2.6	57
165	. *IEEE Journal of Quantum Electronics*, **1994**, 30, 350-365	2	52
164	Macromodeling of single-electron transistors for efficient circuit simulation. *IEEE Transactions on Electron Devices*, **1999**, 46, 1667-1671	2.9	51
163	Application of atomic-force-microscope direct patterning to selective positioning of InAs quantum dots on GaAs. *Applied Physics Letters*, **2000**, 77, 2607-2609	3.4	42

162	Time-convolutionless reduced-density-operator theory of an arbitrary driven system coupled to a stochastic reservoir: Quantum kinetic equations for semiconductors. *Physical Review B*, **1994**, 50, 8310-8318	3.3	37
161	Variational calculations of subbands in a quantum well with uniform electric field: GramSchmidt orthogonalization approach. *Applied Physics Letters*, **1986**, 49, 1450-1452	3.4	34
160	Spontaneous emission rate of green strain-compensated InGaN/InGaN LEDs using InGaN substrate. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 195-198	1.6	33
159	Theory of optical gain in strained-layer quantum wells within the 6 Luttinger Kohn model. *Journal of Applied Physics*, **1995**, 78, 2489-2497	2.5	33
158	Model of the field-effect quantum-well laser with free-carrier screening and valence band mixing. *Journal of Applied Physics*, **1988**, 64, 6143-6149	2.5	32
157	Light emission enhancement in blue InGaAlN/InGaN quantum well structures. *Applied Physics Letters*, **2011**, 99, 181101	3.4	31
156	Final state boundary condition of the Schwarzschild black hole. *Physical Review D*, **2006**, 74,	4.9	31
155	Silicon single-electron transistors with sidewall depletion gates and their application to dynamic single-electron transistor logic. *IEEE Transactions on Electron Devices*, **2002**, 49, 627-635	2.9	31
154	Optical gain of a quantum-well laser with non-Markovian relaxation and many-body effects. *IEEE Journal of Quantum Electronics*, **1996**, 32, 960-965	2	31
153	Cuprous halides semiconductors as a new means for highly efficient light-emitting diodes. *Scientific Reports*, **2016**, 6, 20718	4.9	30
152	Optical gain improvement in type-II InGaN/GaNSb/GaN quantum well structures composed of InGaN/and GaNSb layers. *Applied Physics Letters*, **2010**, 96, 051106	3.4	27
151	Single-electron transistor based on a silicon-on-insulator quantum wire fabricated by a side-wall patterning method. *Applied Physics Letters*, **2001**, 79, 3812-3814	3.4	26
150	Time-convolutionless reduced-density-operator theory of an arbitrary driven system coupled to a stochastic reservoir. II. Optical gain and line-shape function of a driven semiconductor. *Physical Review B*, **1995**, 51, 2159-2166	3.3	26
149	Analytical Threshold Voltage Model Including Effective Conducting Path Effect (ECPE) for Surrounding-Gate MOSFETs (SGMOSFETs) With Localized Charges. *IEEE Transactions on Electron Devices*, **2010**, 57, 3176-3180	2.9	25
148	Theory of non-Markovian gain in strained-layer quantum-well lasers with many-body effects. *IEEE Journal of Quantum Electronics*, **1998**, 34, 344-352	2	24
147	. *IEEE Journal of Quantum Electronics*, **1989**, 25, 2260-2265	2	23
146	Effect of Ti thickness on contact resistance between GaN nanowiresand TiAu electrodes. *Applied Physics Letters*, **2004**, 85, 1636-1638	3.4	22
145	Optical gain in InGaNInGaAlN quantum well structures with zero internal field. *Applied Physics Letters*, **2008**, 92, 171115	3.4	21

144	Electronic and optical properties of staggered InGaN/InGaN quantum-well light-emitting diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 2637-2640	1.6	20
143	Many-body effects on optical gain in strained hexagonal and cubic GaN/AlGaN quantum well lasers. *Applied Physics Letters*, **1997**, 71, 398-400	3.4	20
142	Finite element analysis of valence band structures in quantum wires. *Journal of Applied Physics*, **2004**, 96, 2055-2062	2.5	20
141	Selective growth of InAs self-assembled quantum dots on nanopatterned SiO2/Si substrate. *Applied Physics Letters*, **2001**, 78, 1403-1405	3.4	20
140	Piezoelectric effects on many-body optical gain of zinc-blende and wurtzite GaN/AlGaN quantum-well lasers. *Applied Physics Letters*, **1999**, 75, 1354-1356	3.4	20
139	Fabrication and electrical characterization of planar resonant tunneling devices incorporating InAs self-assembled quantum dots. *Applied Physics Letters*, **1999**, 75, 1167-1169	3.4	20
138	Quantum-state cloning in the presence of a closed timelike curve. *Physical Review A*, **2013**, 88,	2.6	19
137	. *IEEE Journal of Selected Topics in Quantum Electronics*, **1995**, 1, 301-307	3.8	19
136	Theory of polar-optical-phonon scattering in a semiconductor quantum wire. *Journal of Applied Physics*, **1991**, 69, 3596-3600	2.5	18
135	Hawking□Unruh effect and the entanglement of two-mode squeezed states in Riemannian space□time. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2007**, 366, 202-205	2.3	17
134	Electrical conduction measurement of thiol modified DNA molecules. *Superlattices and Microstructures*, **2003**, 34, 433-438	2.8	17
133	Intersubband transitions in a delta -doped semiconductor with an applied electric field: Exact solutions. *Physical Review B*, **1993**, 48, 7981-7985	3.3	17
132	A field-effect quantum-well laser with lateral current injection. *Journal of Applied Physics*, **1988**, 64, 440-442	2.5	17
131	**2011**,		16
130	A SPICE-Compatible New Silicon Nanowire Field-Effect Transistors (SNWFETs) Model. *IEEE Nanotechnology Magazine*, **2009**, 8, 643-649	2.6	14
129	Fabrication of one-dimensional devices by a combination of AC dielectrophoresis and electrochemical deposition. *Nanotechnology*, **2008**, 19, 105305	3.4	14
128	Intervalley interactions in Si quantum dots. *Journal of Applied Physics*, **2005**, 98, 033709	2.5	14
127	Optical gain of InGaP and cubic GaN quantum-well lasers with very strong spin□orbit coupling. *Journal of Applied Physics*, **1996**, 79, 7731-7737	2.5	14

126	Temperature Dependent Study of Random Telegraph Noise in Gate-All-Around PMOS Silicon Nanowire Field-Effect Transistors. *IEEE Nanotechnology Magazine*, **2010**, 9, 754-758	2.6	13
125	Intrinsically p-type cuprous iodide semiconductor for hybrid light-emitting diodes. *Scientific Reports* , **2020**, 10, 3995	4.9	12
124	. *IEEE Transactions on Electron Devices*, **2011**, 58, 2520-2524	2.9	12
123	Internal field engineering in CdZnO/MgZnO quantum well structures. *Applied Physics Letters*, **2009**, 94, 083507	3.4	12
122	Optical Gain in GaN Quantum Well Lasers with Quaternary AlInGaN Barriers. *Japanese Journal of Applied Physics*, **2005**, 44, 7460-7463	1.4	12
121	Qualitative estimation of optical gain in wide-band-gap semiconductor quantum wells. *Journal of Applied Physics*, **1994**, 76, 8206-8208	2.5	12
120	Electric field dependence of intrasubband polar-optical-phonon scattering in a quantum well. *Physical Review B*, **1988**, 37, 2529-2535	3.3	12
119	Langevin noise sources for the Boltzmann transport equations with the relaxation-time approximation in nondegenerate semiconductors. *Journal of Applied Physics*, **1985**, 58, 2262-2265	2.5	12
118	High optical gain of II-VI semiconductor quantum wells for efficient light-emitting devices. *Applied Physics Letters*, **2013**, 102, 121114	3.4	11
117	Microwave Characterization of a Single Wall Carbon Nanotube Bundle. *Japanese Journal of Applied Physics*, **2008**, 47, 4965-4968	1.4	11
116	Optical gain and luminescence of a ZnO-MgZnO quantum well. *IEEE Photonics Technology Letters*, **2006**, 18, 349-351	2.2	11
115	Optical gain of strained hexagonal and cubic GaN quantum-well lasers. *Applied Physics Letters*, **1996** , 69, 3303-3305	3.4	11
114	Generation of Local Magnetic Field by Nano Electro-Magnets. *Japanese Journal of Applied Physics*, **2004**, 43, 2054-2056	1.4	10
113	Spontaneous Polarization and Piezoelectric Effects on Inter-Subband Scattering Rate in Wurtzite GaN/AlGaN Quantum-Well. *Japanese Journal of Applied Physics*, **2001**, 40, L941-L944	1.4	10
112	Internal field effects on electronic and optical properties of ZnO/BeZnO quantum well structures. *Physica B: Condensed Matter*, **2014**, 441, 12-16	2.8	9
111	Intersubband transition in lattice-matched BGaN/AlN quantum well structures with high absorption coefficients. *Optics Express*, **2017**, 25, 3143-3152	3.3	9
110	Observation of three-dimensional shell filling in cylindrical silicon nanowire single electron transistors. *Applied Physics Letters*, **2007**, 90, 182102	3.4	9
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108	Screening Effects on Electron-Longitudinal Optical-Phonon Intersubband Scattering in Wide Quantum Well and Comparison with Experiment. *Japanese Journal of Applied Physics*, **2000**, 39, 6601-6605	1.4	9
107	Nano-Structure Fabrication and Manipulation by the Cantilever Oscillation of an Atomic Force Microscope. *Japanese Journal of Applied Physics*, **1999**, 38, 7257-7259	1.4	9
106	Screening effects on the band-gap renormalization of strained InGaAs/InGaAsP quantum well lasers lattice matched to GaAs. *Applied Physics Letters*, **1996**, 68, 1844-1846	3.4	9
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104	Effect of indirect interband absorption in Ge/SiGe quantum wells. *Journal of Applied Physics*, **2011**, 110, 083119	2.5	8
103	Electronic transport properties of a single-wall carbon nanotube field effect transistor with deoxyribonucleic acid conjugation. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1115-1117	3	8
102	Microwave design and characterization of a cryogenic dip probe for time-domain measurements of nanodevices. *Review of Scientific Instruments*, **2004**, 75, 2455-2460	1.7	8
101	Electrical Transport Properties of Au-Doped Deoxyribonucleic Acid Molecules. *Japanese Journal of Applied Physics*, **2005**, 44, 2623-2625	1.4	8
100	Band-structure engineering of a cubic GaN quantum-well laser. *IEEE Photonics Technology Letters*, **1996**, 8, 194-196	2.2	8
99	Strained II-VI Quantum Well for a Room-Temperature Blue-Green Laser. *Japanese Journal of Applied Physics*, **1992**, 31, L556-L559	1.4	8
98	Theoretical analysis of strained-layer InGaAs/GaAs quantum-well lasers with gain suppression and valence-band mixing. *Applied Physics Letters*, **1992**, 60, 548-550	3.4	8
97	Electric-field dependence of the intersubband optical absorption in a semiconductor quantum well. *Superlattices and Microstructures*, **1988**, 4, 153-157	2.8	8
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94	Magnetotransport measurements through stacked InAs self-assembled quantum dots. *Applied Physics Letters*, **2003**, 82, 1230-1232	3.4	7
93	Entanglement generates entanglement: entanglement transfer by interaction. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2005**, 338, 192-196	2.3	7
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91	. *IEEE Journal of Quantum Electronics*, **1993**, 29, 2864-2872	2	7

90	Theoretical Studies on TM-Polarized Light Emission for Ultraviolet BAlGaN/AlN Optoelectronic Devices. *IEEE Photonics Technology Letters*, **2016**, 28, 2153-2155	2.2	6
89	Spontaneous emission and optical gain characteristics of blue InGaAlN/InGaN quantum well structures with reduced internal field. *Journal of Applied Physics*, **2012**, 112, 043107	2.5	6
88	Dispersive full-wave finite-difference time-domain analysis of the bipolar cylindrical cloak based on the effective medium approach. *Journal of the Optical Society of America B: Optical Physics*, **2013**, 30, 140	1.7	6
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86	Transport Properties of a DNA-Conjugated Single-Wall Carbon Nanotube Field-Effect Transistor. *Japanese Journal of Applied Physics*, **2009**, 48, 06FD08	1.4	6
85	Electronic Properties of InGaAs/GaAs Strained Coupled Quantum Dots Modeled by Eight-Bandk □pTheory. *Japanese Journal of Applied Physics*, **2003**, 42, 144-149	1.4	6
84	Exciton Binding Energies in Zincblende GaN/AlGaN Quantum Wells. *Japanese Journal of Applied Physics*, **2004**, 43, 140-143	1.4	6
83	Quantum circuit optimization using quantum Karnaugh map. *Scientific Reports*, **2020**, 10, 15651	4.9	6
82	Experimental realization of Schumacher's information geometric Bell inequality. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2021**, 405, 127444	2.3	6
81	High optical polarization ratio of semipolar (202□1□)-oriented InGaN/GaN quantum wells and comparison with experiment. *Journal of Applied Physics*, **2012**, 112, 093106	2.5	5
80	A wide dynamic range analog predistortion-type linearizer using self-cancellation scheme. *IEEE Microwave and Wireless Components Letters*, **2005**, 15, 661-663	2.6	5
79	Fabrication of quantum dot transistors incorporating a single self-assembled quantum dot. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 7, 430-434	3	5
78	Intraband Relaxation Time in Wurtzite GaN/InAlN Quantum-Well. *Japanese Journal of Applied Physics*, **1999**, 38, L815-L818	1.4	5
77	Theoretical aspects of blue-green II□VI strained quantum well lasers. *Physica B: Condensed Matter*, **1993**, 191, 140-155	2.8	5
76	Collision broadening of optical gain in semiconductor lasers. *Journal of Applied Physics*, **1989**, 65, 4517-4520	2.5	5
75	Optical Emission Characteristics of Pseudopolarization-Matched Green AlInGaN/InGaN Quantum Well Structures. *IEEE Journal of Selected Topics in Quantum Electronics*, **2013**, 19, 1-8	3.8	4
74	Elliptic cylindrical pseudo-optical black hole for omnidirectional light absorber. *Journal of the Optical Society of America B: Optical Physics*, **2014**, 31, 1948	1.7	4
73	Full-wave finite-difference time-domain analysis of the invisibility cloak mapped to a line segment with isotropic complementary media. *Journal of the Optical Society of America B: Optical Physics*, **2013**, 30, 2148	1.7	4

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70	Faraday's Induction Experiment in Nano-Transformers. *IEEE Nanotechnology Magazine*, **2008**, 7, 120-123	2.6	4
69	Non-Markovian gain and luminescence of an InGaN-AlInGaN quantum-well with many-body effects. *IEEE Journal of Quantum Electronics*, **2005**, 41, 1253-1259	2	4
68	Gate bias controlled NDR in an in-plane-gate quantum dot transistor. *Physica E: Low-Dimensional Systems and Nanostructures*, **2006**, 32, 532-535	3	4
67	Formation of Electrical Interconnects by Self-Trapping of Deoxyribonucleic Acid Molecules. *Japanese Journal of Applied Physics*, **2004**, 43, 3803-3805	1.4	4
66	Fabrication and characterization of metal-semiconductor field-effect-transistor-type quantum devices. *Journal of Applied Physics*, **2004**, 96, 704-708	2.5	4
65	Theoretical study of strained InGaP quantum-well lasers. *Applied Physics Letters*, **1995**, 66, 628-630	3.4	4
64	First-order correction to phonon scattering due to dynamical screening in quantum wells. *Physical Review B*, **1994**, 50, 1713-1716	3.3	4
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61	Effect of boron incorporation on light emission characteristics of UV BAlGaN/AlN quantum well structures. *Applied Physics Express*, **2016**, 9, 021001	2.4	3
60	Unruh effect as a noisy quantum channel. *Physical Review A*, **2018**, 98,	2.6	3
59	Dispersive finite-difference time-domain (FDTD) analysis of the elliptic cylindrical cloak. *Journal of the Korean Physical Society*, **2012**, 60, 1349-1360	0.6	3
58	Electronic structure of p(2 □) Ag films on Si(100). *Journal of the Korean Physical Society*, **2013**, 62, 86-91	0.6	3
57	Effects of wetting layer on exciton binding energy of strained CdTe/ZnTe pyramidal quantum dots. *Solid State Communications*, **2015**, 204, 61-63	1.6	3
56	Hybrid InGaN/CdZnO quantum well structures for optoelectronic applications in the short wavelength spectral region. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 378-381	1.3	3
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53	Transport study of ultra-thin SOI MOSFETs. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 19, 39-43	3	3
52	Optical Gain in Wurtzite ZnO/ZnMgO Quantum Well Lasers. *Japanese Journal of Applied Physics*, **2005**, 44, L1403-L1406	1.4	3
51	Single-Electron Transistors with Sidewall Depletion Gates on a Silicon-On-Insulator Nano-Wire. *Japanese Journal of Applied Physics*, **2002**, 41, 2574-2577	1.4	3
50	Spontaneous polarization and piezoelectric effects on intraband relaxation time in a wurtzite GaN/AlGaN quantum well. *Applied Physics A: Materials Science and Processing*, **2000**, 71, 589-592	2.6	3
49	Modeling of Semiconductor Nanowire Field-Effect Transistors Considering Schottky-Barrier-Height Lowering. *Journal of the Korean Physical Society*, **2007**, 51, 298	0.6	3
48	Intersubband absorption coefficients of GaN/AlN and strain-compensated InGaN/InAlN quantum well structures. *Superlattices and Microstructures*, **2016**, 100, 508-513	2.8	3
47	Dip-Shaped AlGaN/AlN Light-Emitting Diodes With Delta-Layer Containing Boron. *IEEE Photonics Technology Letters*, **2017**, 29, 1042-1045	2.2	2
46	Theoretical study of optical properties of non-polar BAlGaN/AlN quantum wells lattice-matched to AlN. *Solid State Communications*, **2019**, 290, 67-69	1.6	2
45	Investigation of humidity-dependent size control of local anodic oxidation on graphene by using atomic force microscopy. *Journal of the Korean Physical Society*, **2015**, 66, 617-620	0.6	2
44	Optical Gain Characteristics in GaAsPN/GaPN Quantum Well Lasers for Silicon Integration. *IEEE Journal of Selected Topics in Quantum Electronics*, **2015**, 21, 153-159	3.8	2
43	Optical polarization characteristics of m-plane InGaN/GaN quantum well structures and comparison with experiment. *Applied Physics Letters*, **2013**, 103, 101107	3.4	2
42	Intersubband absorption of p-type wurtzite GaN/AlN quantum well for fiber-optics telecommunication. *Journal of Applied Physics*, **2017**, 122, 184303	2.5	2
41	Full wave finite-difference time-domain study of lossless acoustic bipolar cylindrical cloak with compressed geometry and complementary media. *Journal of Applied Physics*, **2015**, 118, 044508	2.5	2
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39	Black hole state evolution, final state and Hawking radiation. *Classical and Quantum Gravity*, **2012**, 29, 224007	3.3	2
38	Enhancement of light power for strain-compensated hybrid InGaN/InGaN/MgZnO light-emitting diodes. *Applied Physics Letters*, **2010**, 97, 121107	3.4	2
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35	Transmission-Type Radio-Frequency Single-Electron Transistor with In-Plane-Gate Single-Electron Transistor. *Japanese Journal of Applied Physics*, **2007**, 46, 2592-2595	1.4	2
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33	An automated glitch-detection/restoration method of atomic force microscope images. *Review of Scientific Instruments*, **2002**, 73, 3245-3250	1.7	2
32	Calculations of hole–phonon scattering in strained-layer quantum wells. *Journal of Applied Physics*, **1995**, 78, 4505-4509	2.5	2
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28	Effects of Confinement on the Valley Splitting of Si Quantum Structures. *Journal of the Korean Physical Society*, **2008**, 53, 3322-3327	0.6	2
27	A Bottom-gate Depletion-mode Nanowire Field Effect Transistor(NWFET) Model Including a Schottky Diode Model. *Journal of the Korean Physical Society*, **2009**, 55, 1162-1166	0.6	2
26	Theoretical studies on light emission characteristics of high-efficiency BInGaN/GaN quantum well structures with blue spectral range. *Superlattices and Microstructures*, **2016**, 96, 150-154	2.8	2
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23	Explicit continuous current-voltage (I-V) models for fully-depleted surrounding-gate MOSFETs (SGMOSFETs) with a finite doping body. *Journal of Nanoscience and Nanotechnology*, **2010**, 10, 3316-20	1.3	1
22	Single-electron tunneling in silicon-on-insulator nano-wire transistors. *Superlattices and Microstructures*, **2003**, 34, 245-251	2.8	1
21	Optical gain control model of the quantum-well laser diode. *Journal of Applied Physics*, **1991**, 70, 5246-5253	2.5	1
20	Gain Switching in Coupled Quantum Wells. *Japanese Journal of Applied Physics*, **1992**, 31, 1055-1058	1.4	1
19	Temperature-Dependent Polarized Photoluminescence from c-plane InGaN/GaN Multiple Quantum Wells Grown on Stripe-Shaped Cavity-Engineered Sapphire Substrate. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900526	1.3	1

18	A model for the InGaAs/InP single photon avalanche diodes with multiple-quantum wells in the charge multiplication region. *Journal of the Korean Physical Society*, **2018**, 72, 289-293	0.6	0
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15	Strain and built-in potential effects on optical properties of wurtzite GaN/AlInN quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2019**, 108, 112-115	3	0
14	Strain relaxation effects on TE-polarized light emission and in-plane polarization ratio in c-plane ultraviolet AlGaN/AlN quantum well structures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2020**, 120, 114112	3	
13	Effect of Coupled Quantum-Dot Insertion on the Radiative Recombination Probability of Wurtzite InGaN/GaN Quantum Dots. *Journal of the Korean Physical Society*, **2020**, 76, 55-58	0.6	
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7	DC Transport Characteristics of Lambda DNA Molecules and Effect of RF Signals. *Japanese Journal of Applied Physics*, **2006**, 45, 5471-5473	1.4	
6	Graded InGaAs/GaAs strained-layer single quantum well laser. *Applied Physics Letters*, **1993**, 62, 2239-2241	3.4	
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4	Reply to Comment on 'Magnetic bead detection using nano-transformers'. *Nanotechnology*, **2016**, 27, 418002	3.4	
3	P-type wurtzite GaN/AlGaN quantum well structures for normal incidence inter-subband photodetectors at 1.55 μm. *Applied Physics Express*, **2018**, 11, 114001	2.4	
2	Equivalent circuit model of semiconductor nanowire diode by SPICE. *Journal of Nanoscience and Nanotechnology*, **2007**, 7, 4089-93	1.3	
1	Fabrication of poly-silicon nano-wire transistors on plastic substrates. *Journal of Nanoscience and Nanotechnology*, **2007**, 7, 4150-3	1.3	